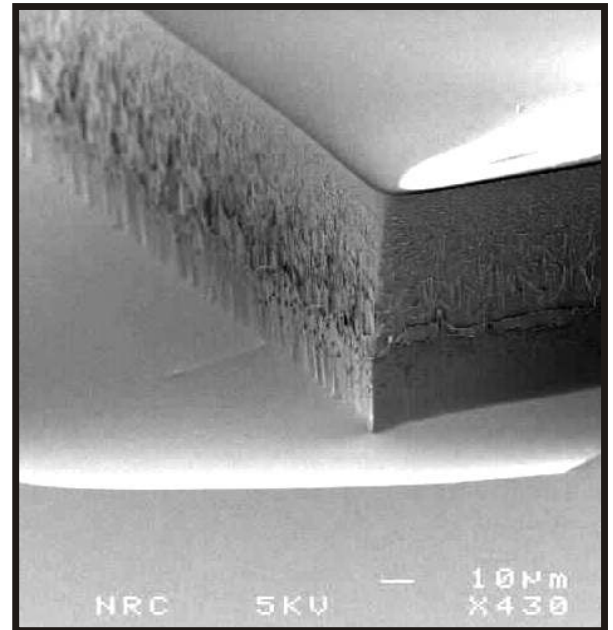
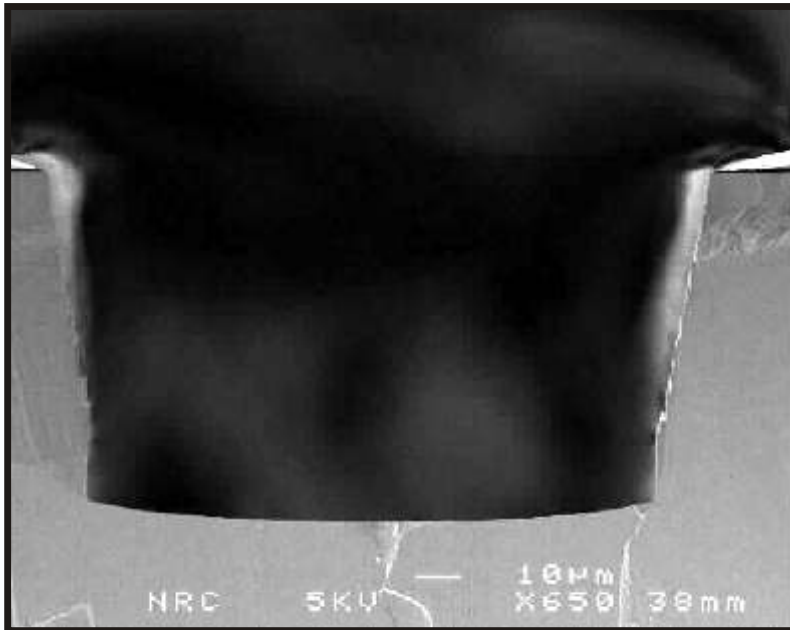


# Plasmalab Data

## Deep GaP ICP Etching



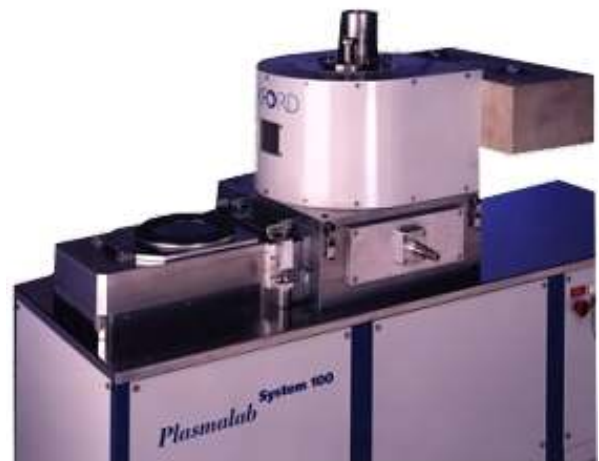
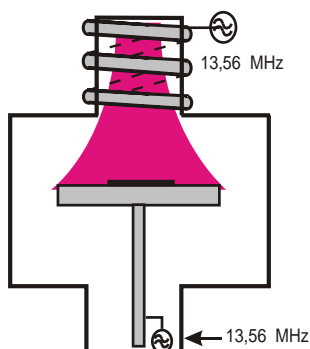
### Technology:

Reactive Ion Etching  
with ICP Source (2 or 13 MHz)  
Inductive Coupled Plasma  
RF driven substrate electrode

Courtesy of National Research Council, Ottawa (Dr B. Lamontagne):  
80 µm deep anisotropic GaP etch

### Results:

Rate : 2.6 µm/ min  
good uniformity  
selectivity to PR > 12 : 1  
selectivity to SiO<sub>2</sub> mask 120 : 1



*Plasmalab System 100*